

# Identifying diverging-effective mass in MOSFET and ${}^3\text{He}$ systems\*

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## Abstract

Emerging devices such as a neuromorphic device and a qubit can use the Mott transition phenomenon, but in particular, the diverging mechanism of the phenomenon remains to be clarified. The diverging-effective mass near Mott insulators was measured in strongly correlated Mott systems such as a fermion  ${}^3\text{He}$  and a Si metal-oxide-semiconductor-field-effect transistor, and is closely fitted by the effective mass obtained by the extension of the Brinkman-Rice(BR) picture,  $m^*/m = 1/[1 - (U/U_c)^2] = 1/(1 - \kappa_{BR}^2 \rho^4)$  when  $\kappa_{BR}^2 \approx 1 (\neq 1)$ , where  $0 < U/U_c = \kappa_{BR} \rho^2 < 1$ , correlation strength is  $\kappa_{BR}$ , band-filling is  $\rho$ . Its identification is a percolation of a constant mass in the Brinkman-Rice picture. Over  $\kappa_{BR} \approx 0.96$  is evaluated.

**Keywords:** Insulator-Metal Transition, Mott insulator, diverging-effective mass, Brinkman-Rice picture

## I. INTRODUCTION

The diverging-effective mass (DEM) in a strongly correlated metallic Mott system [1] is evidence of strong correlation between fermions that often occurs in condensed phenomena such as superconductivity, superfluid, the Mott transition, and a fractional quantum Hall effect. The characteristics of the DEM can be very important to reveal the mechanism of the phenomena. Although the DEM has been measured in materials such as  $\text{Sr}_{1-x}\text{La}_x\text{TiO}_3$  [2],  $\text{VO}_2$  [3] a 2-dimensional (dim) fermion  ${}^3\text{He}$  [4, 5], a dilute 2-dim metal-oxide-semiconductor-field-effect transistor (MOSFET) [6], and a superconductor  $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$  [7], the identification of the DEMs still remains to be revealed [8].

## II. PROPOSED METHOD

Here, the metal-insulator transition (MIT) theory with the DEM is briefly reviewed for less than and one electron per atom. The DEM, the inverse of discontinuity,  $d$ , at  $E_F$  [1], means the increase of the number of carriers outside  $E_F$ ,

$$\begin{aligned} \frac{1}{d} &\equiv \frac{m^*}{m} = \frac{1}{[1 - (U/U_c)^2]}, \\ &= \frac{1}{(1 - \kappa_{BR}^2 \rho^4)}. \end{aligned} \quad (1)$$

This can be satisfied when the Coulomb-repulsion ratio  $0 < U/U_c = \kappa_{BR} \rho^2 < 1$ , band filling  $0 < \rho = n_{\text{metal}}/n_{\text{tot}} \leq 1$ , correlation strength  $0 < U/U_c = \kappa \leq 1$  when  $\rho=1$  half filling. In these expressions,  $n_{\text{metal}}$  is the carrier density in the metal region,  $n_{\text{tot}}$  is the number of all atomic sites in the measurement region, and  $U_c$  is the critical Coulomb interaction [1] [9, 10]. Eq. (1) was derived by an extension of the Brinkman-Rice (BR) picture using a fractional effective charge (or fractron),  $e^* = \rho e$ , averaged over all atomic sites in the measurement region [9–11]. The Mott insulator at  $U/U_c=1$  is assumed when  $\rho=1$ . Existence of a DEM in a hole-doping region where  $n = n_{\text{tot}} - n_c$  (about 0.02% from Mott criterion [12]) can be seen as a hole-driven Mott MIT. Eq. (1) gives a measurable quantity that represents the average of the true  $m^*/m$  in the BR picture. Moreover, the BR picture [1] was also confirmed in the metallic side of  $d = \infty$  Hubbard model [13]. The DEM was observed in  ${}^3\text{He}$  at high density [4], which is a prototype system for the strongly correlated

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system. This is explained in Figs. 1A and 1B, which shows that the quantity  $\rho = n/n_{tot}$  increases as the  $^3\text{He}$  density increases (where  $n_{tot} \approx 5.101 \text{ nm}^{-2}$ ). The increasing  $\rho$  induces a DEM, as per Eq. (1), which closely fits the experimental data (Fig. 1B). Another example helps clarify the diverging thermoelectric power measured in Si-MOSFET systems [6]. As the carrier density decreases,  $\rho = n_c/n_s$  increases (Fig. 2C). This is why the extent of metal region is constant (about 0.02%) - because a conducting path with lower resistance is formed in the channel of MOSFET after the insulator-to-metal transition occurs. The DEM data for this system [4] are closely fitted by Eq. (1) (Fig. 2D).

### III. CONCLUSIONS

In conclusion, the DEM identified in many Mott systems is the effect of measurement due to inhomogeneity and percolation phenomenon. The true value of the DEM in such systems is the renormalized constant mass in the BR picture [1]. The correlation strengths in  $^3\text{He}$  and MOSFET systems associated with the DEM are  $\kappa_{BR} \approx 0.96$  ( $m^*/m \approx 13$ ) determined from  $m^*/m = 1/(1 - \kappa_{BR}^2)$  in assuming  $\rho_c \equiv n/n_c \approx 0.98$  when  $\rho \approx 1$ . This reveals that the  $^3\text{He}$  system and the MOSFET system are strongly correlated. Diverging in thermoelectric power is also attributed to the DEM. The Mott transition near  $\rho=1$  can be used for future emerging devices such as a neuromorphic device and a qubit.

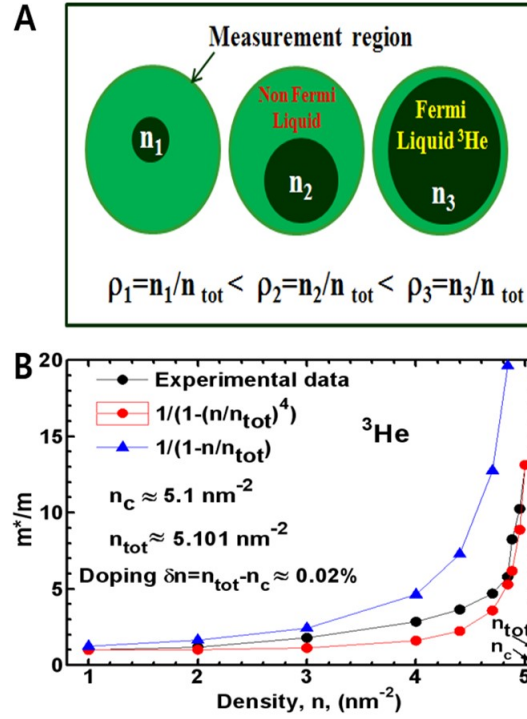


FIG. 1: (A) Schematic diagram understanding the Fermi-liquid region in a  $^3\text{He}$  (hole doping) system with monolayer.  $n_i = n_{Fermi}$  and  $n_{non-Fermi}$  are particle densities in black and green regions, respectively, and  $n_{tot} = n_{Fermi} + n_{Non-Fermi}$ . Band filling,  $\rho_i = n_i/n_{tot}$ , is given. As  $n_i$  increases,  $\rho_i$  increases; this is a percolation phenomenon. (B) Experimental data [4] and fittings using Eq. (1) when  $\kappa_{BR} \approx 1 (\neq 1)$  are shown.

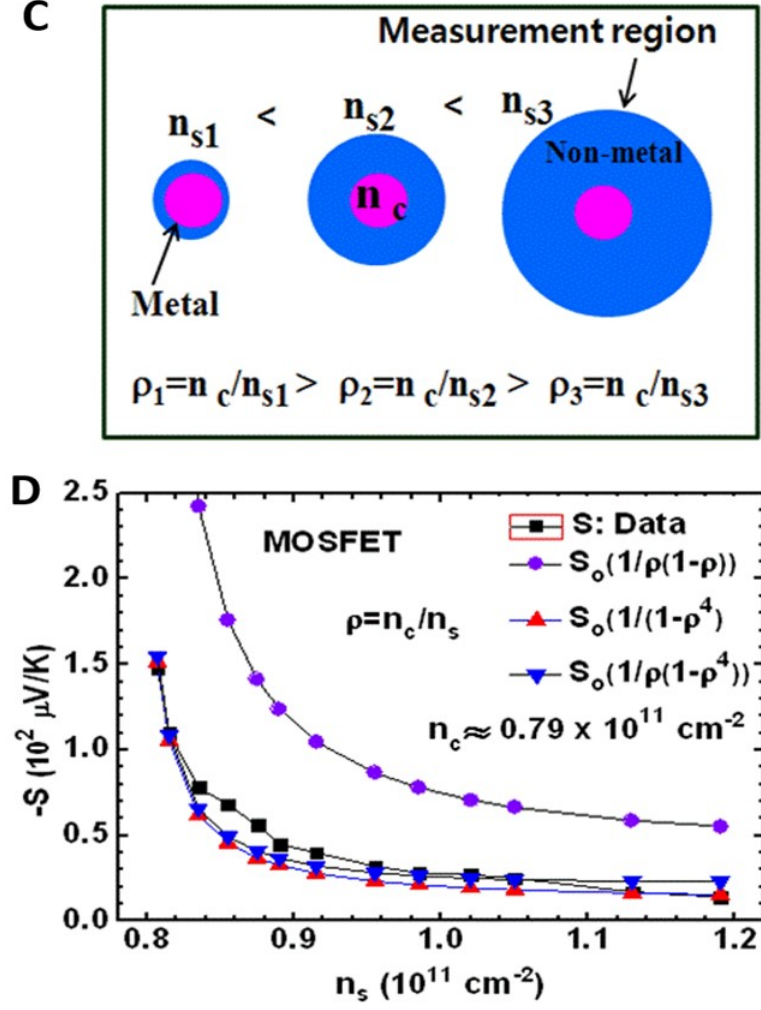


FIG. 2: (C) Schematic diagram of the metal region in a Si-MOSFET (electron doping). Although the carrier density,  $n_s$ , increases, the extent of the metal phase (pink region) with  $n_c \approx 0.79 \times 10^{11} \text{ cm}^{-2}$  is constant (about 0.02% to  $n_{Si} \approx 3.4 \times 10^{14} \text{ cm}^{-2}$  in Si), but  $n_{non}$  in the non-metal region (blue region) increases (the increase of the measurement region);  $n_{tot} \equiv n_s = n_c + n_{non}$ . Given  $\rho = n_c/n_s$  increases as  $n_s$  decreases. (D) Experimental data extracted from the thermoelectric power measured at 0.8 K [6] is closely fitted by Eq. (1). The thermoelectric power of metal,  $S = (\alpha \pi^3 k_B^2 T / 3e)(1/E_F) = (8\alpha \pi^3 k_B^2 T / 3h^2)(m^*/e^* n_c) = S_o(1/\rho)(1/(1-\rho^4))$ , is given, where  $e^* = \rho e$  [9–11],  $\rho = n_c/n_s$ ,  $T = 0.8$  K,  $m^* = m_o/(1-\rho^4)$ ,  $\alpha = 0.6$ , and  $S_o = (8\alpha \pi^3 k_B^2 T / 3h^2)(m_o/e n_c) \approx 20.6$  are used.

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